

# Silicon Carbide (SiC) Schottky Diode – EliteSiC, 30 A, 650 V, D2, D2PAK-2L

## FFSB3065B

### Description

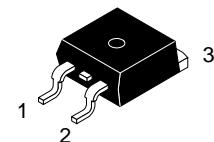
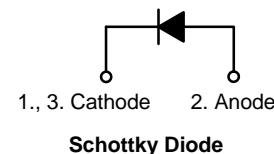
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

### Features

- Max Junction Temperature 175°C
- Avalanche Rated 144 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

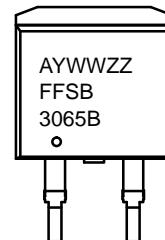
### Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



D<sup>2</sup>PAK2 (TO-263-2L)  
CASE 418BK

### MARKING DIAGRAM



A	= Assembly Site
YWW	= Date Code (Year & Week)
ZZ	= Lot Code
FFSB3065B	= Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FFSB3065B

## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage		650	V
$E_{AS}$	Single Pulse Avalanche Energy (Note 1)		144	mJ
$I_F$	Continuous Rectified Forward Current @ $T_C < 25^\circ\text{C}$		73	A
	Continuous Rectified Forward Current @ $T_C < 139^\circ\text{C}$		30	
$I_{F, Max}$	Non-Repetitive Peak Forward Surge Current	$T_C = 25^\circ\text{C}, 10 \mu\text{s}$	1100	A
		$T_C = 150^\circ\text{C}, 10 \mu\text{s}$	1000	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current $T_C = 25^\circ\text{C}$	Half-Sine Pulse, $t_p = 8.3 \text{ ms}$	120	A
$P_{tot}$	Power Dissipation		$T_C = 25^\circ\text{C}$	246
			$T_C = 150^\circ\text{C}$	41
$T_J, T_{STG}$	Operating and Storage Temperature Range		-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1.  $E_{AS}$  of 144 mJ is based on starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.5 \text{ mH}$ ,  $I_{AS} = 24 \text{ A}$ ,  $V = 50 \text{ V}$ .

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.61	°C/W

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
$V_F$	Forward Voltage	$I_F = 30 \text{ A}, T_C = 25^\circ\text{C}$	–	1.38	1.7	V
		$I_F = 30 \text{ A}, T_C = 125^\circ\text{C}$	–	1.6	2.0	
		$I_F = 30 \text{ A}, T_C = 175^\circ\text{C}$	–	1.72	2.4	
$I_R$	Reverse Current	$V_R = 650 \text{ V}, T_C = 25^\circ\text{C}$	–	0.5	40	μA
		$V_R = 650 \text{ V}, T_C = 125^\circ\text{C}$	–	1	80	
		$V_R = 650 \text{ V}, T_C = 175^\circ\text{C}$	–	2	120	
$Q_C$	Total Capacitive Charge	$V = 400 \text{ V}$	–	74	–	nC
$C$	Total Capacitance	$V_R = 1 \text{ V}, f = 100 \text{ kHz}$	–	1280	–	pF
		$V_R = 200 \text{ V}, f = 100 \text{ kHz}$	–	139	–	
		$V_R = 400 \text{ V}, f = 100 \text{ kHz}$	–	108	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping*
FFSB3065B	FFSB3065B	D <sup>2</sup> PAK2 (TO-263-2L) (Pb-Free / Halogen Free)	800 / Tape & Reel

\*For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

**TYPICAL CHARACTERISTICS**  
( $T_J = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)

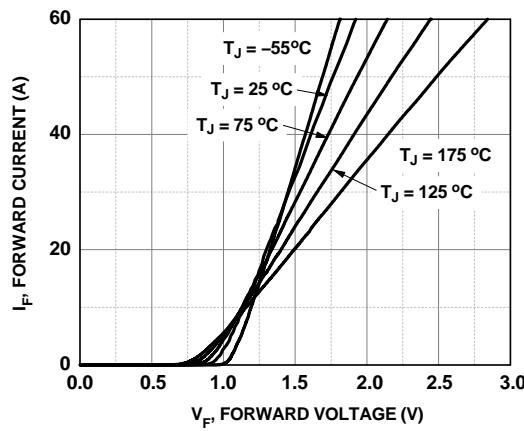


Figure 1. Forward Characteristics

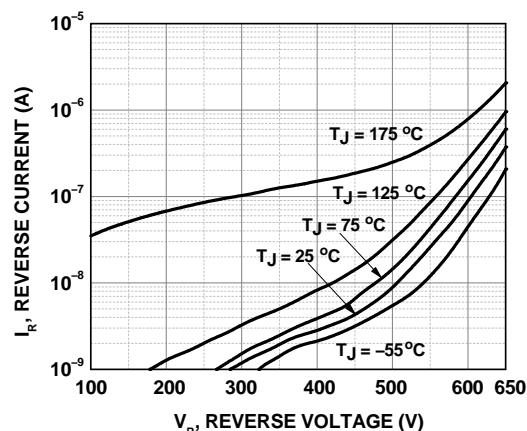


Figure 2. Reverse Characteristics

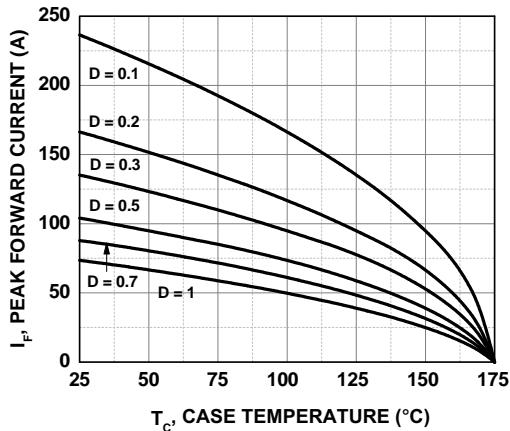


Figure 3. Current Derating

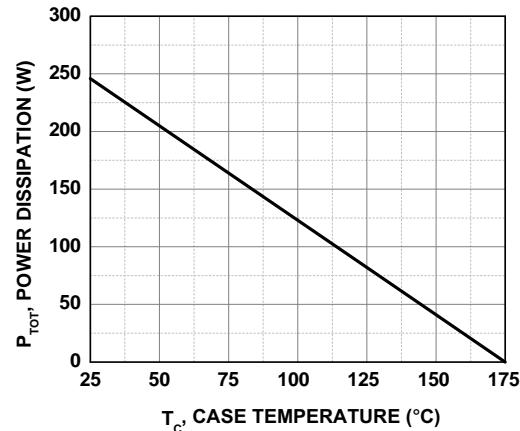


Figure 4. Power Derating

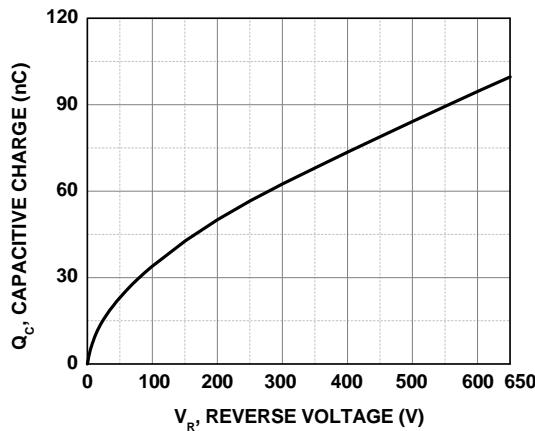


Figure 5. Capacitive Charge vs. Reverse Voltage

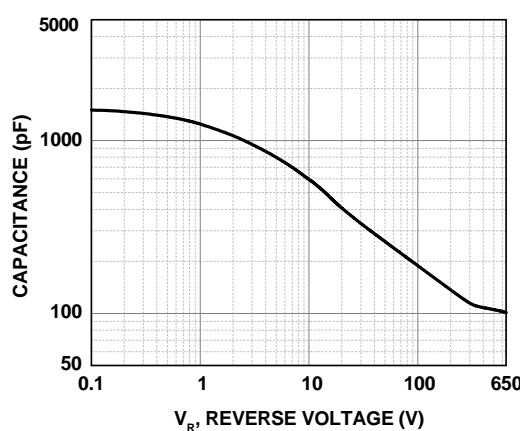


Figure 6. Capacitance vs. Reverse Voltage

# FFSB3065B

## TYPICAL CHARACTERISTICS

( $T_J = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)

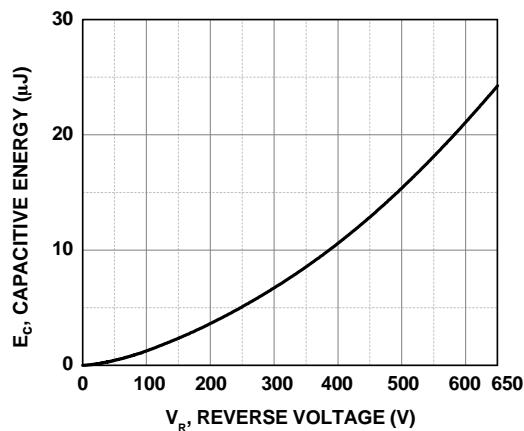


Figure 7. Capacitance Stored Energy

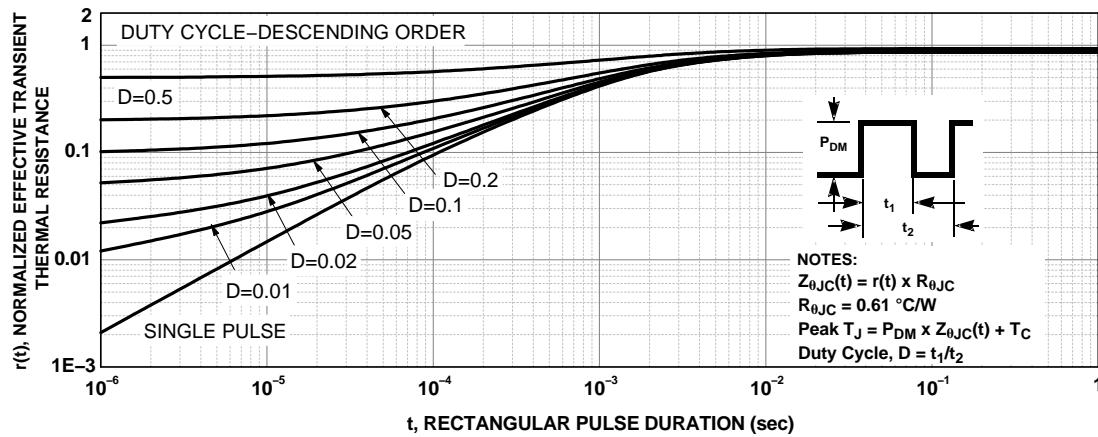


Figure 8. Junction-to-Case Transient Thermal Response Curve

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## TEST CIRCUIT AND WAVEFORMS

$L = 0.5 \text{ mH}$

$R < 0.1 \Omega$

$V_{DD} = 50 \text{ V}$

$EAVL = 1/2LI^2 [V_{R(AVL)} / (V_{R(AVL)} - V_{DD})]$

$Q1 = \text{IGBT } (BV_{CES} > \text{DUT } V_{R(AVL)})$

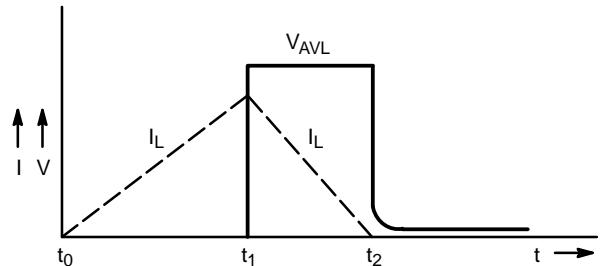
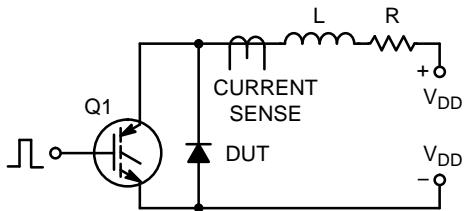
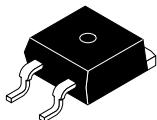
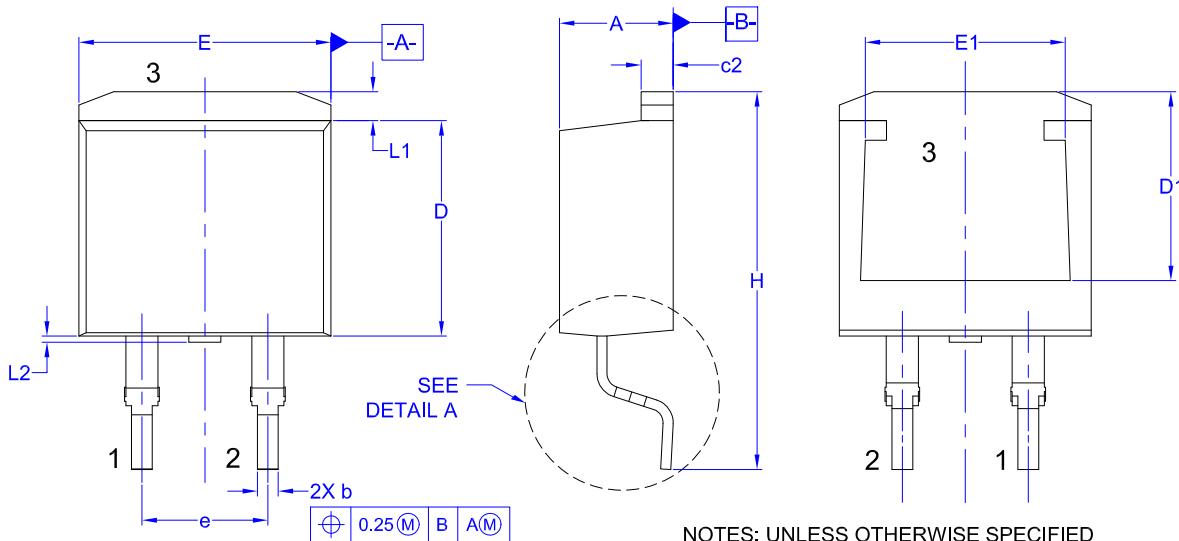


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

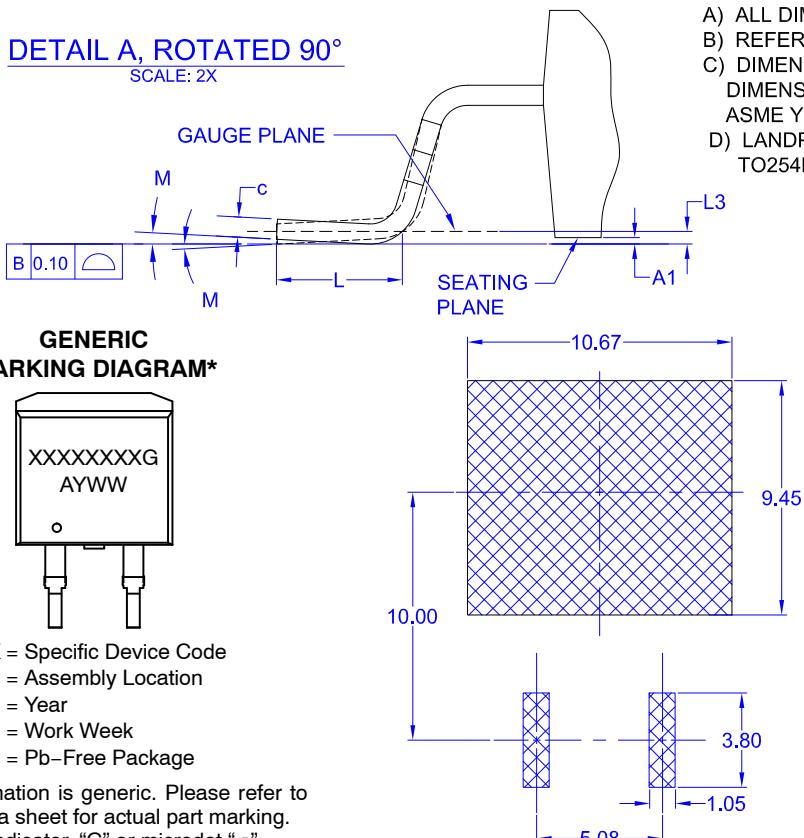


**D<sup>2</sup>PAK2 (TO-263-2L)**  
CASE 418BK  
ISSUE O

DATE 02 AUG 2018



DETAIL A, ROTATED 90°  
SCALE: 2X



NOTES: UNLESS OTHERWISE SPECIFIED  
 A) ALL DIMENSIONS ARE IN MILLIMETERS.  
 B) REFERENCE JEDEC, TO-263, VARIATION AB.  
 C) DIMENSIONING AND TOLERANCING PER  
 ASME Y14.5 - 2009.  
 D) LANDPATTERN RECOMMENDATION PER IPC  
 TO254P1524X482-3N

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.06	4.57	4.83
A1	0.00	0.10	0.25
b	0.51	0.81	0.99
c	0.30	0.407	0.74
c2	1.14	1.30	1.65
D	8.38	8.69	9.65
D1	7.30	7.80	8.30
E	9.65	10.16	10.67
E1	8.00	8.62	9.00
e	5.08 BSC		
H	14.60	15.35	15.88
L	1.78	2.54	2.79
L1	0.90	1.29	1.68
L2	0.00	0.15	0.25
L3	0.25 BSC		
M	0°	4°	8°

LAND PATTERN RECOMMENDATION  
UNLESS NOTED, ALL DIMS TYPICAL

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DESCRIPTION:	D <sup>2</sup> PAK2 (TO-263-2L)	PAGE 1 OF 1

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